

ABSTRACT

A manufacturing method of a Ta sputtering target in which a Ta ingot or billet formed by melting and casting is subject to forging, annealing, rolling processing
5 and the like to prepare a sputtering target, wherein the ingot or billet is forged and thereafter subject to recrystallization annealing at a temperature of 1373K to 1673K. As a result of improving and devising the forging process and heat treatment process, the crystal grain diameter can be made fine and uniform, and a method of stably manufacturing a Ta sputtering target superior in characteristics can be
10 obtained thereby.